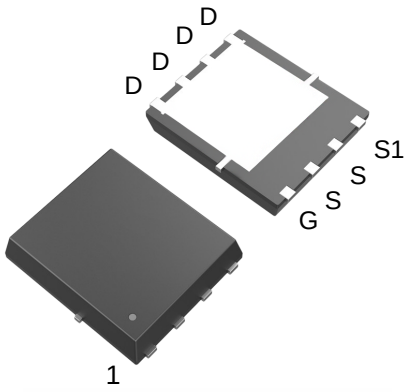
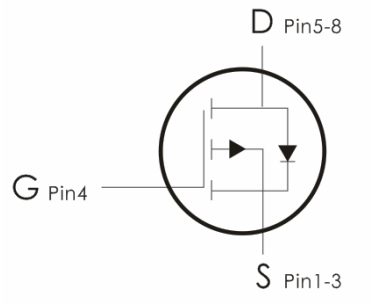
Description：

This P-Channel MOSFET uses advanced SGT technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.





Features：

1) V_{DS}=-100V,I_D=-30A,$R_{DS(ON)}$<55mΩ @V_{GS}=-10V（Typ：45mΩ）
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.
6) MSL3

Package Marking and Ordering Information：

Part NO.	Marking	Package	Packing
DON30P10T	30P10T	DFN5*6-8	5000 pcs/Reel

Absolute Maximum Ratings：(T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	-30	A
	Continuous Drain Current-T_C=100℃	-21	
I_{DM}	Pulsed Drain Current[1]	-120	
P_D	Power Dissipation	78	W
E_{AS}	Single pulse avalanche energy[2]	78	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	1.6	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	102	℃/W

Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	-100	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=-100V	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	-1	-1.8	-2.5	V
$R_{DS(ON)}$	Drain-Source On Resistance[3]	V_{GS}=-10V,I_D=-20A	---	45	55	mΩ
		V_{GS}=-4.5V,I_D=-10A	---	55	65	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-50V, V_{GS}=0V, f=1MHz	---	2100	---	pF
C_{oss}	Output Capacitance		---	176	--	
C_{rss}	Reverse Transfer Capacitance		---	27	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=-50V, I_D=-20A, R_G=5Ω,V_{GS}=-10V	---	8.6	---	ns
t_r	Rise Time		---	20.5	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	65.9	---	ns
t_f	Fall Time		---	43.4	---	ns
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-50V, I_D=-20A	---	38	---	nC
Q_{gs}	Gate-Source Charge		---	6.7	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	7.1	---	nC
Drain-Source Diode Characteristics						
I_S	Continuous Drain Curren	V_D=V_G=0V	---	---	-30	A
I_{SM}	Pulsed Drain Current		---	---	-120	A
Trr	Reverse Recovery Time	I_S=20A,T_J=25,dI/dt=100A/us	---	68	---	ns
Qrr	Reverse Recovery Charge		---	200	---	nC
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=-20A	---	---	-1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition : TJ=25℃,VDD=50V,V_G=10V,L=0.5mH
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics: (T_C=25℃ unless otherwise noted)

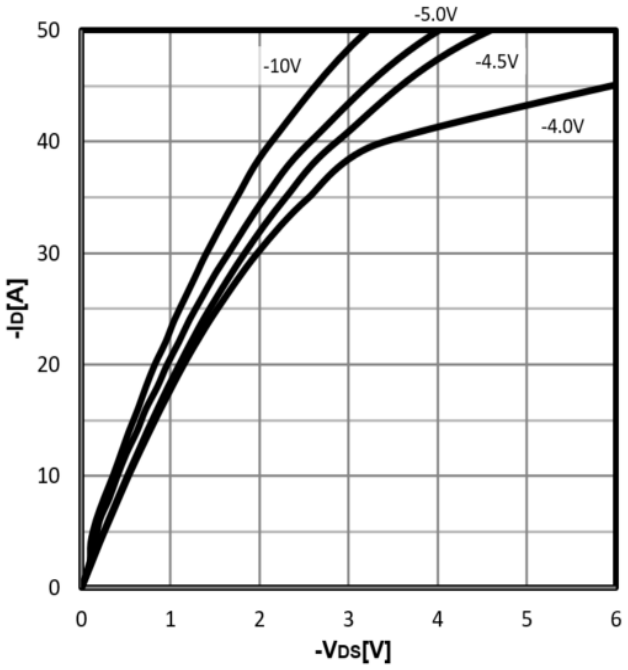


Figure1: Typ. output characteristics
$-I_D=f(-V_{DS})$

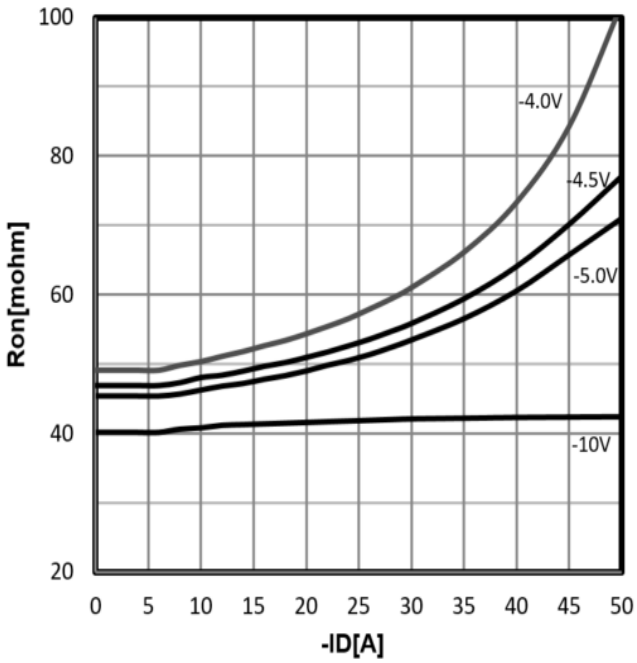


Figure 2: Typ. drain-source on resistance
$R_{DS(on)}=f(-I_D)$

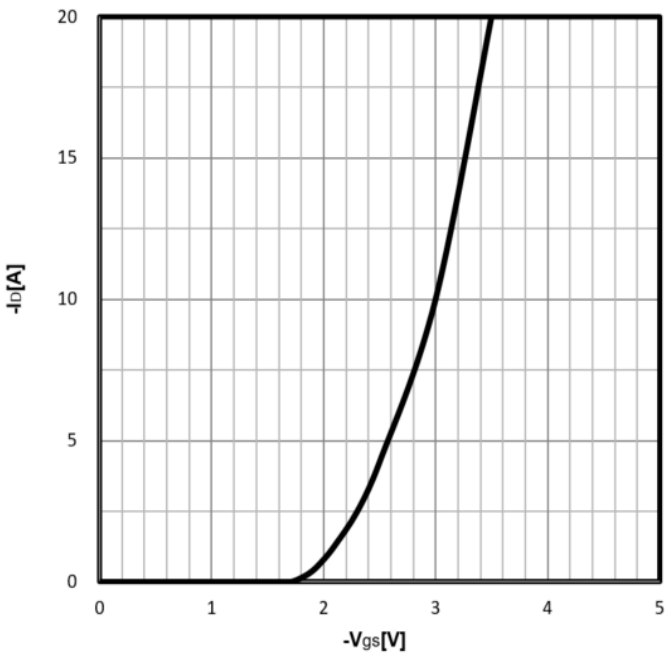


Figure 3: Typ. transfer characteristics
$-I_D=f(-V_{GS})$

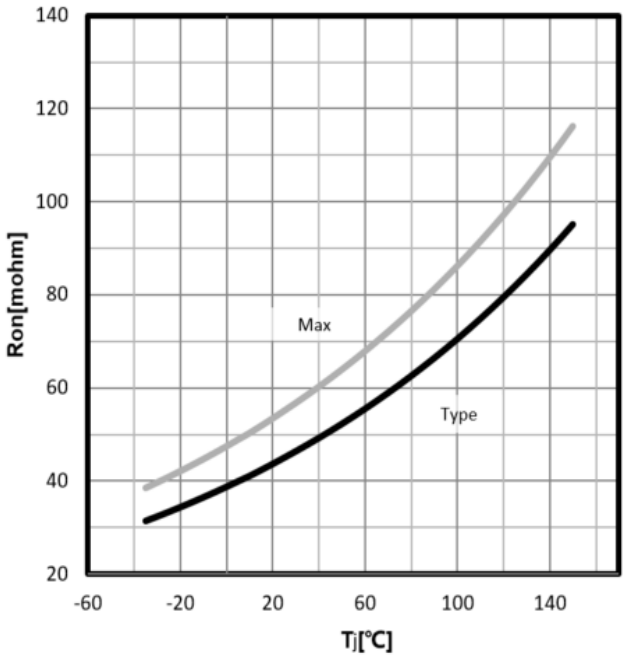


Figure 4: Drain-source on-state resistance
$R_{DS(on)}= f(T_j)$; I_D=-5A; V_{GS}=-10V

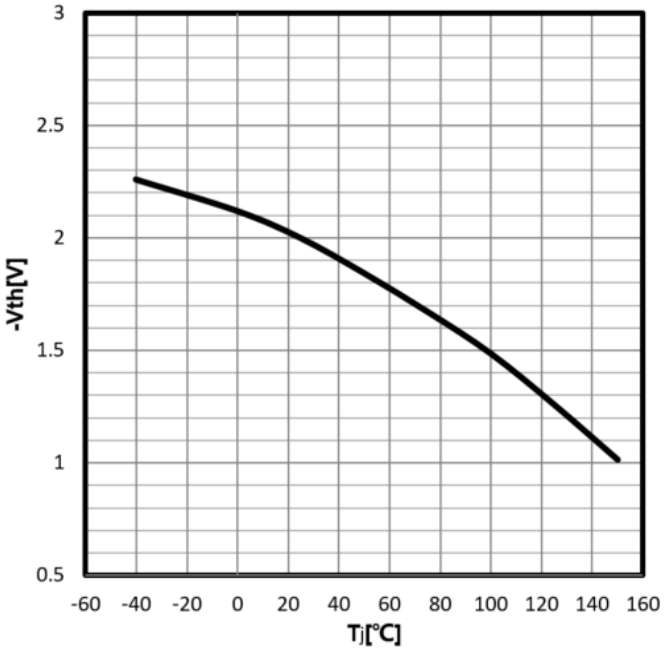


Figure 5 Gate Threshold Voltage
$-V_{TH}=f(T_j)$; $I_D=-250uA$

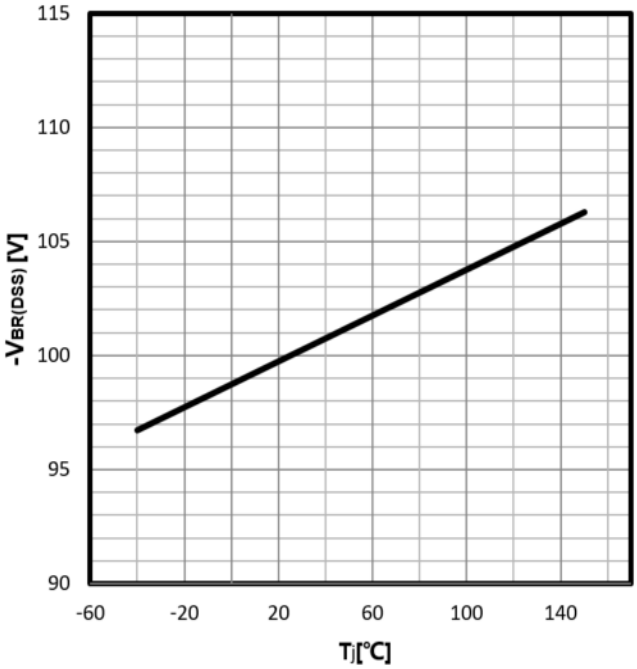


Figure 6: Drain-source breakdown voltage
$-V_{BR(DSS)}=f(T_j)$; $I_D=-250uA$

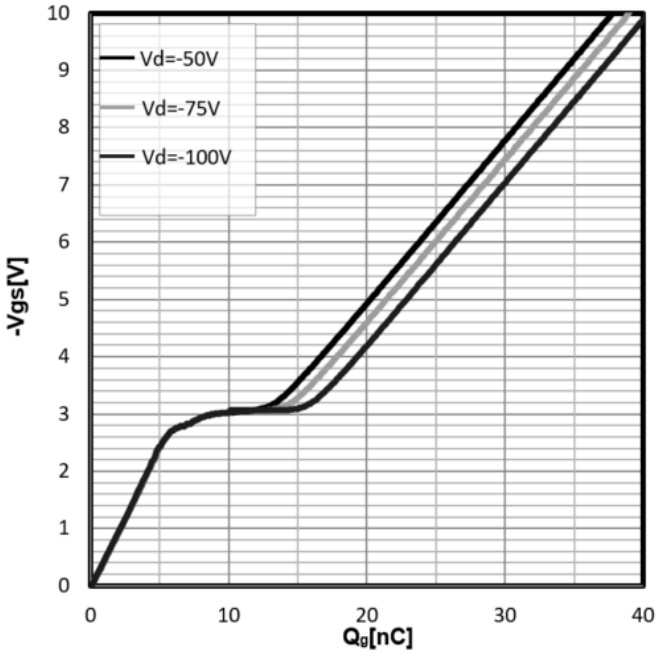


Figure 7: Typ. gate charge
$-V_{GS}=f(Q_g)$; $I_D=-5A$

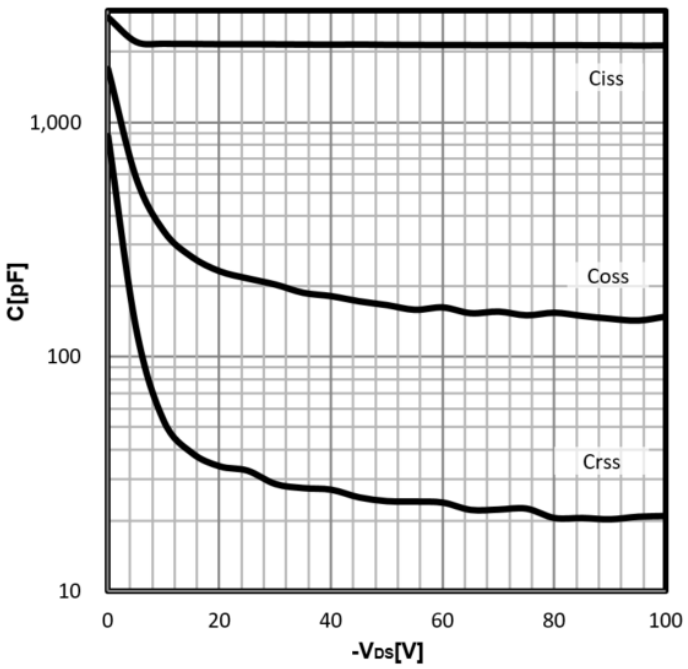


Figure 8: Typ. capacitances
C =f(-V_{DS}); V_{GS}=0V; f =1MHz

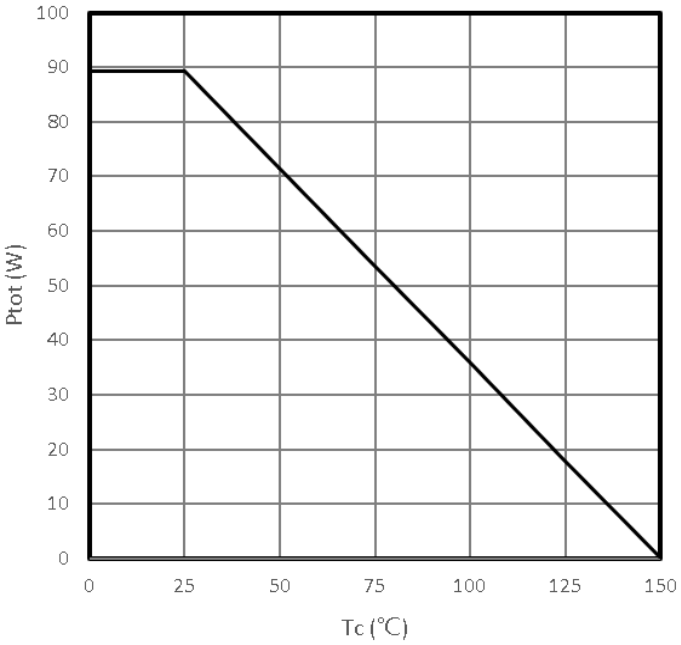


Figure 9: Power Dissipation
$P_{tot}=f(T_C)$

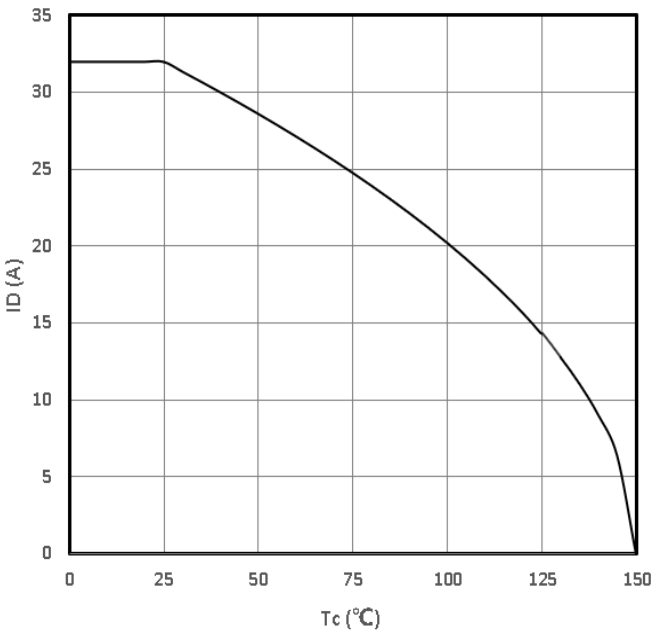


Figure 10: Maximum Drain Current
$-I_D=f(T_C)$

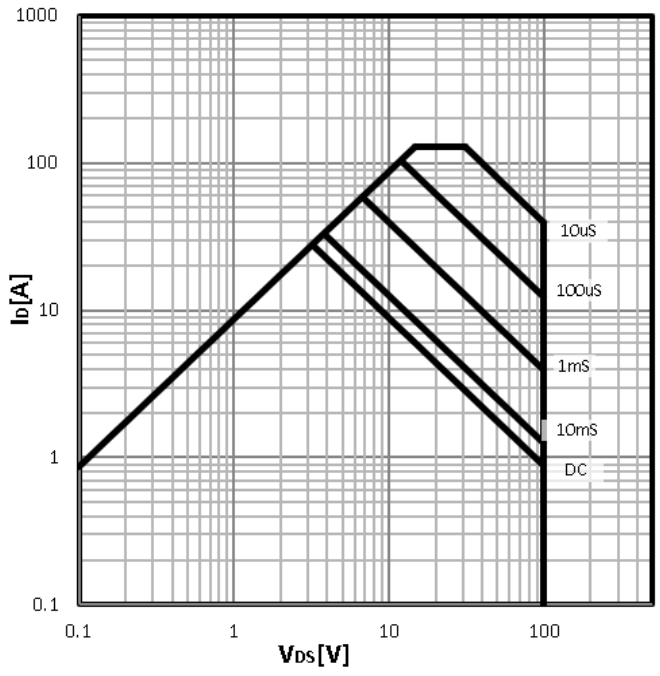


Figure.11: Safe operating area
$-I_D=f(-V_{DS})$

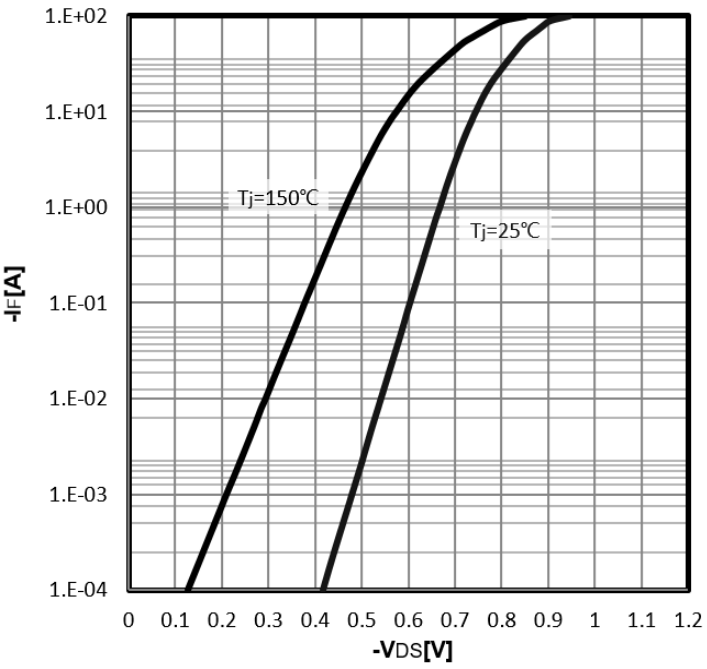


Figure 12 Body Diode Forward Voltage Variation
$-I_F=f(-V_{DS})$

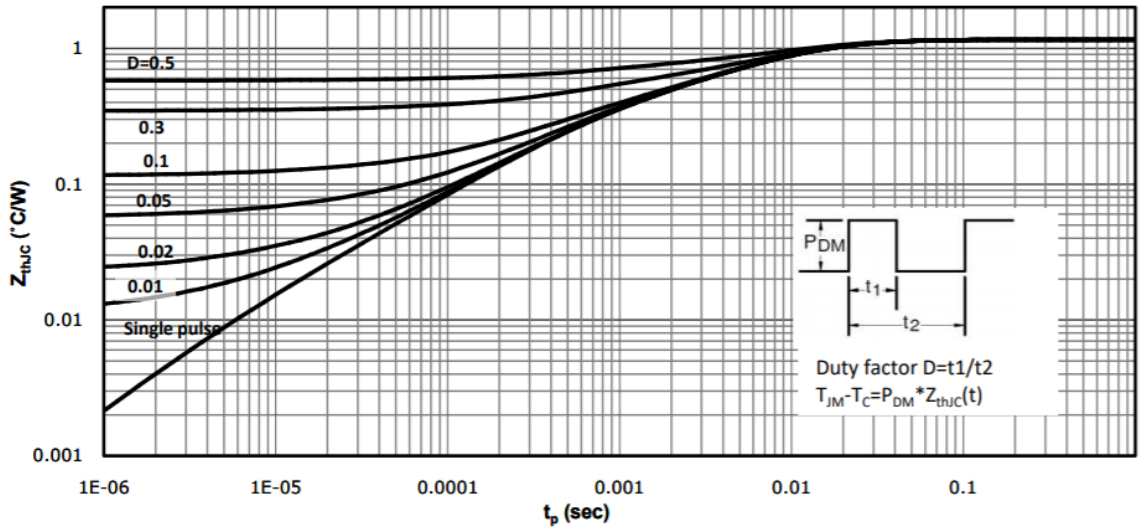
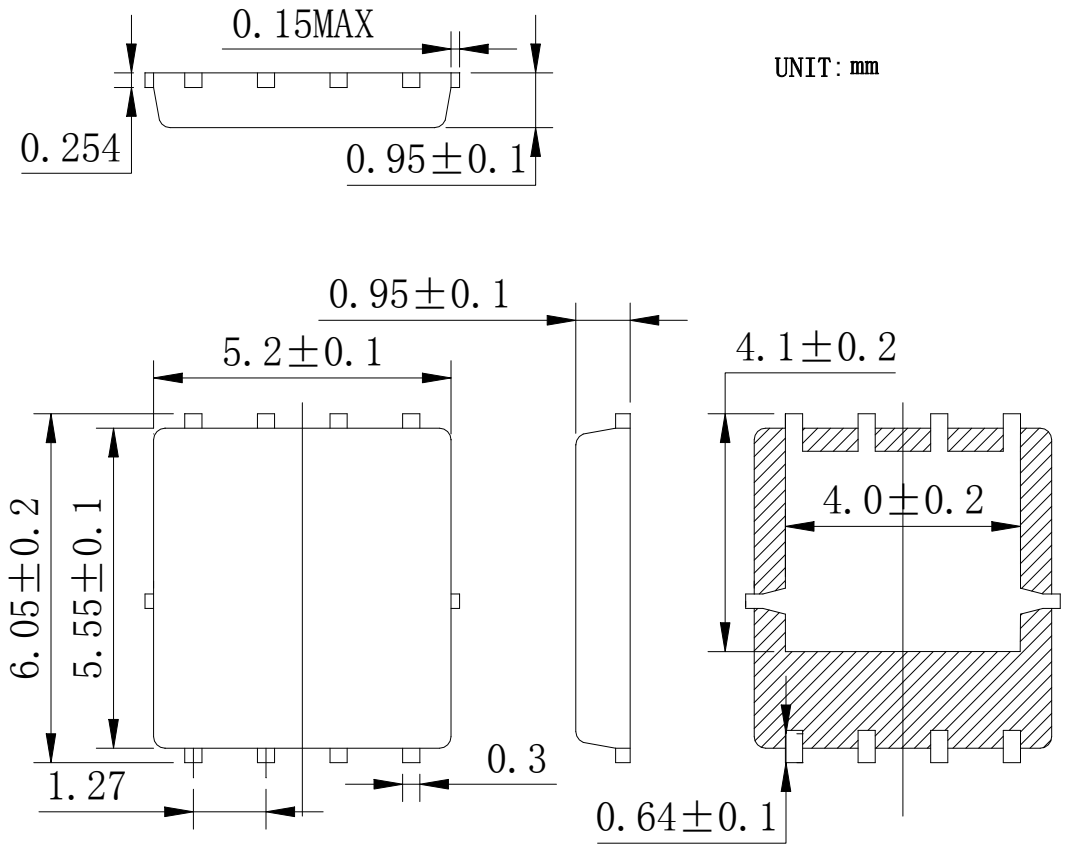


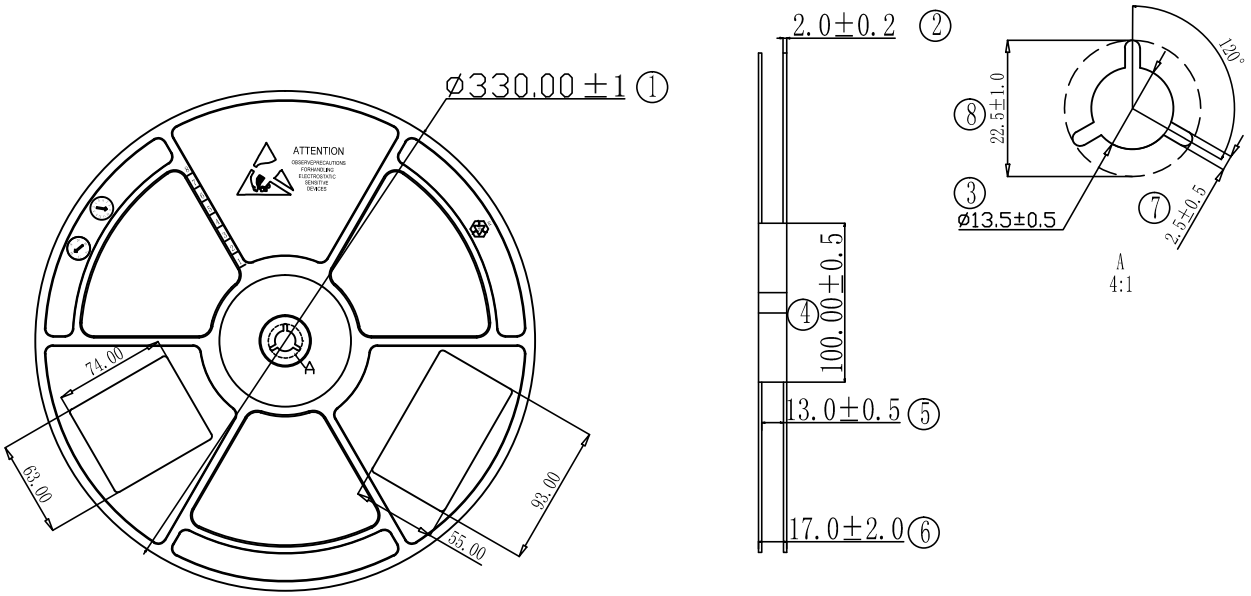
Figure 13 Max. transient thermal impedance
$Z_{thJC}=f(t_p)$

DFN5×6-8 Package Information：

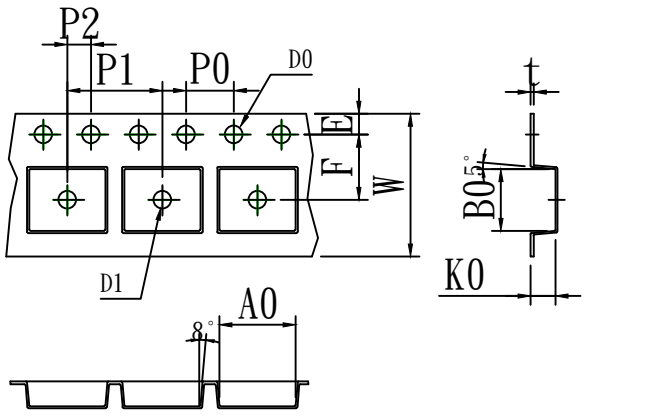


Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	6.15±0.10	5.40±0.10	1.30±0.10	1.55±0.10	1.55±0.10	4.00±0.10	8.00±0.10	40.00±0.10
Symbol	W	E	F	P2	t			
Spec	12.00±0.10	1.75±0.10	5.50±0.10	2.00±0.10	0.20±0.05			



Pulling direction

Marking Information：

①. Doingter LOGO

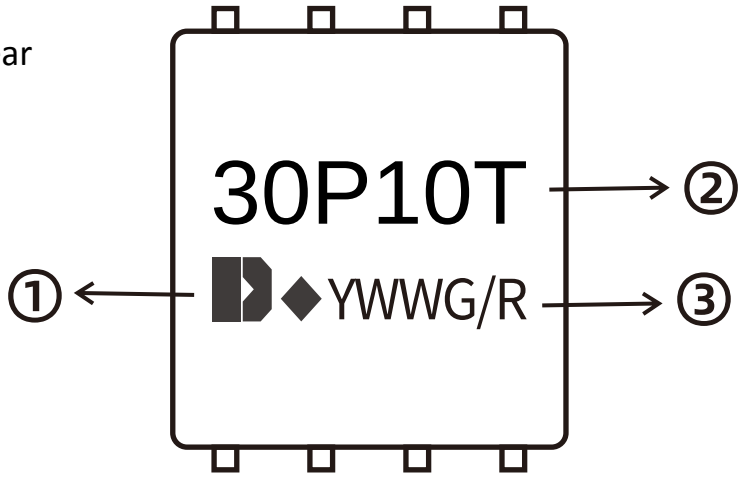
②. Part NO.

③. Date Code(YWWG / R)

Y：Year Code , last digit of the year

WW：Week Code(01-53)

G/R：G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2024-12-19	Release of final version

Attention :

- Information furnished in this document is believed to be accurate and reliable. However, Shenzhen Doingter Semiconductor Co.,Ltd. assumes noresponsibility for the consequences of use without consideration for such information nor use beyond it.
- Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Shenzhen Doingter complies with the agreement. Products and information provided in this document have no infringement of patents.
- Shenzhen Doingter assumes noresponsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied. Is a registered trademark of Shenzhen Doingter Semiconductor Co., Ltd.